(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization

International Bureau



(10) International Publication Number

WO 2021/064742 A1

08 April 2021 (08.04.2021)

(51) International Patent Classification: C09K 11/54 (2006.01) H010 1/22 (2006.01) H010 1/00 (2006,01)

(21) International Application Number:

PCT/IN2020/000020

(22) International Filing Date:

29 September 2020 (29.09.2020)

(25) Filing Language:

English English

(26) Publication Language:

(30) Priority Data: 201931039488

30 September 2019 (30.09.2019) IN

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0M

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, OA, RO, RS, RU, RW,

(54) Title: ZNS NANO PARTICLE THIN FILM DEPOSITED METAMATERIAL ANTENNA FOR NOTCH FREQUENCY AP-PLICATION

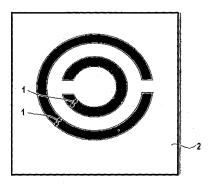


Fig.1

(57) Abstract: A ZnS Nanoparticle Thin Film Deposited Metamaterial Antenna For Notch Frequency Application comprising of a 20-25 nm ZnS nanomaterial thin film grown in the gap(1) of a complementary split ring resonator (CSRR) unit cell(2). The method comprises of the steps- (a)boiling Zn salt solution at 100°C and then adding 1/5th the volume of 1.1%, chitosan in mild acetic acid (1-2%) and then adding aqueous Na₂S in stoichiometric amounts; (b) allowing the solution to cool and then centrifuging the solution at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain a ZnS calleid which is then alcottened at 4000-5000 mm to obtain at 4000-5000 rpm to obtain a ZnS colloid which is then electrosterically stabilized by chitosan capping; (c)covering the conducting at 4000-5000 rpm to obtain a ZnS colloid which is then electrosterically stabilized by chitosan capping; (c)covering the conducting portion of the CSRR unit cell with a tape and then dropping ZnS colloid obtained from step (b) on it and then drying the unit cell at 80°-90°C; (d) repeating the step(c) for 3 to 5 times. This antenna results in the return loss parameter (S₁₁) getting significantly improved at its resonant frequency at its resonant frequency.

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